

PATENT ABSTRACTS OF JAPAN

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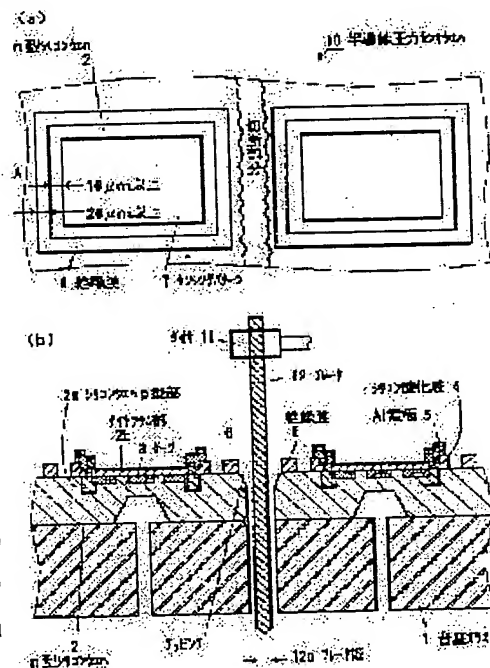
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(54) METHOD FOR CUTTING SEMICONDUCTOR WAFER

(57)Abstract:

PROBLEM TO BE SOLVED: To cut a semiconductor wafer without chipping the wafer.

SOLUTION: In a method for cutting semiconductor wafer, an n-type silicon wafer 2 having a diaphragm section 26 is formed on pedestal glass 1 and a plurality of rectangular sensing patterns 7 composed of gauges 3, Al electrodes 5, silicon oxide films 4, etc., are formed on the section 2b in a grid-like state. In the circumference of each sensing pattern 7, an insulating film 6 having a width of about $\geq 20\mu\text{m}$ is formed at an interval of about $\geq 10\mu\text{m}$ from the pattern 7 (a). The interval between adjacent insulating films 6 is made larger than the width 12a of the blade 12 of a dicer 11 so that the blade 6 cannot come into contact with the insulating films 6 at the time of cutting the wafer 2 with the dicer 11 (b). Thus a semiconductor pressure sensor wafer 10 is constituted.



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